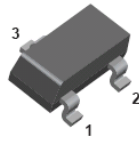
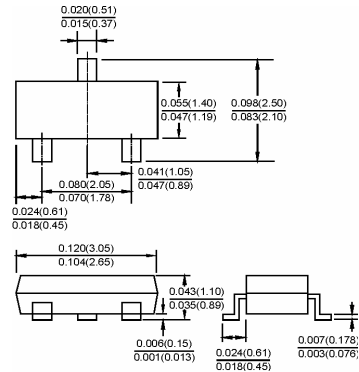


MMBD352-355

Dual Hot Carrier Mixer Diodes



SOT-23



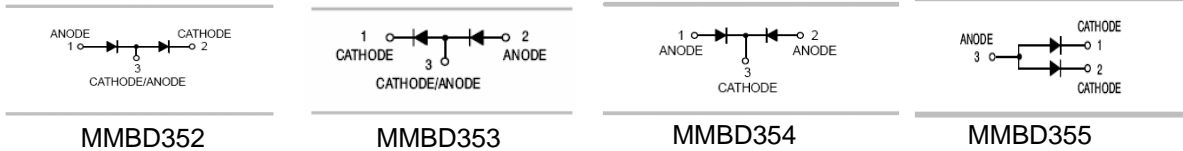
Features

- Very low capacitance—
Less than 1.0pF @ zero V.
- Low forward voltage— $I_F=10\text{mA}$.
- Power dissipation $P_d=300\text{mW}$
- Pb/RoHS Free

Applications

- Designed primarily for UHF mixer applications.

Dimensions in inches and (millimeters)



Ordering Information

Type No.	Marking	Package Code
MMBD352	M5G	SOT-23
MMBD353	M4F	SOT-23
MMBD354	M6H	SOT-23
MMBD355	MJ1	SOT-23

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Limits	Unit
Continuous reverse voltage	V_R	7.0	V
Power Dissipation	P_d	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and storage temperature	T_J, T_{STG}	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)}$	7.0			V	$I_R=100\mu\text{A}$
Forward voltage	V_F			0.60	V	$I_F=10\text{mA}$
Reverse current	I_R			0.25 10	μA	$V_R=3.0\text{V}$ $V_R=7.0\text{V}$
Diode Capacitance	C_D		1.0		pF	$V_R=0\text{V}, f=1\text{MHz}$

MMBD352-355

Dual Hot Carrier Mixer Diodes

TYPICAL CHARACTERISTICS @ $T_A=25^\circ\text{C}$ unless otherwise specified

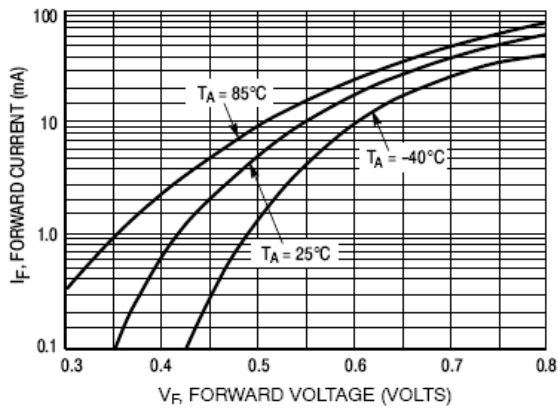


Figure 1. Forward Voltage

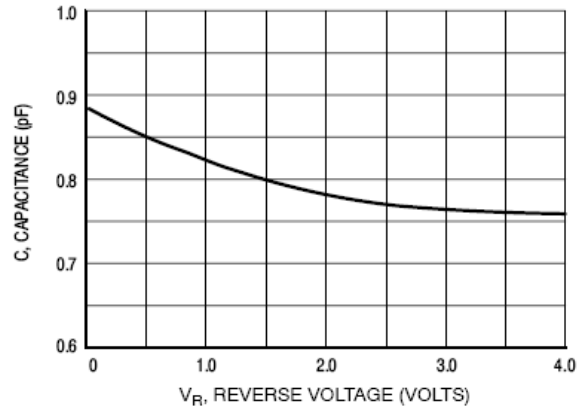


Figure 2. Capacitance